

FORM PTO-1449 (Additional references)
Page 1 of 1

Atty. Docket No.:
H26341 D1
(1139.1124103)

Serial No.:
10/617,290

**LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT**

Applicant: Ralph H. Johnson et al.

Filing Date

Group Art:

July 10, 2003

unknown

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Examiner Initial	Document No.	Date	Name	Filing Date If Appropriate
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FORM PTO-1449	Atty. Docket No.: H26341 D1 (1139.1124103)	Serial No.: 10/617,290
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Applicant:	
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FORM PTO-1449 (References cited in parent application serial no. <u>09/724,820</u>)	Atty. Docket No.: H26341 D1 (1139.1124103)	Serial No.: 10/617,290
Page 2 of 13		
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Applicant: Ralph H. Johnson et al.	
	Filing Date: July 10, 2003	Group Art: unknown

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Atty. Docket No.:
H26341 D1
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Serial No.:
10/617,290

**LIST OF PATENTS AND PUBLICATIONS FOR
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Filing Date:
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Atty. Docket No.:
H26341 D1
(1139.1124103)

Serial No.:
10/617,290

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Applicant: Ralph H. Johnson et al.

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Applicant: Ralph H. Johnson et al.

Filing Date:
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Page 9 of 13		
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	Applicant: Ralph H. Johnson et al.	
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Page 10 of 13		
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Page 11 of 13		
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Page 12 of 13		
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